



UV-reduction of graphene oxide and its application as an interfacial layer to reduce the back-transport reactions in dye-sensitized solar cells

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ABSTRACT

A mixture of graphene oxide (GO) and TiO₂ nanocomposites was reduced photocatalytically by UV-irradiation and applied as interfacial layer between a fluorine doped tin oxide (FTO) layer and a nanocrystalline TiO₂ film. Impedance spectra implied a decreased back-transport reaction of electrons. The graphene–TiO₂ interfacial layer effectively reduced the contact between I₃⁻ ions in the electrolyte and FTO layer, which inhibited back-transport reaction. The introduction of graphene–TiO₂ increased V_{oc} by 54 mV and the photoconversion efficiency was improved from 4.89% to 5.26%.

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1. Introduction

Dye-sensitized solar cells (DSSCs) have attracted considerable attention due to their low production cost and relatively high energy conversion efficiency [1,2]. Highest photovoltaic conversion efficiencies so far reported for DSSCs is about 11% [3]. TiO₂ nanoparticles with average particle size 15–20 nm are typically deposited as a porous layer with a thickness of 10–12 μm on a transparent conductive oxide (TCO) [4,5]. Electrons generated by the dye molecules have to pass through numerous grain boundaries in order to reach TCO through the conduction band of TiO₂. It was suggested that the rough surface of fluorine doped tin oxide (FTO) glass might short circuit the cells [6]. When the thick TiO₂ layer is formed by doctor blade method, the rough FTO surface may not be covered uniformly by the TiO₂ particles (for example Degussa P25 has particle size 25 nm). This can lead to the formation of some voids between the TiO₂ nanoparticles and FTO glass interface [7]. In addition, TiO₂ nanoparticles have a tendency to form large colloids in suspension or paste. Some parts of the FTO surface are not covered by TiO₂ and can directly contact with electrolytes, thereby decreasing V_{oc} by the electron back-transport reaction [FTO(2e⁻) + I₃⁻ → FTO + 3I⁻]. Therefore, controlling the interface between FTO and TiO₂ layer is essential for the formation of efficient DSSCs.

Two-dimensional graphene has attracted much attention on account of their remarkable electronic properties with 0 eV band gap in which the filled valence band touches the conduction band [8], highlighting its application in future optoelectronic devices [9,10]. However, the electrical resistance of graphene oxide is quite high.

Many studies have been reported the reduction of graphene oxides, such as, chemical reduction using reducing agents [11], high temperature annealing [12] and UV-assisted photocatalytic reduction [13]. However, hazardous chemicals (hydrazine or NaBH₄) are used for chemical reduction, and temperatures ~1100 °C are required for thermal reduction.

This Letter reports the UV-assisted photocatalytic reduction of graphene oxide mixed with TiO₂ nanoparticles without the need for hazardous chemicals and high temperature annealing. This graphene–TiO₂ was applied as an interfacial layer between FTO layer and nanocrystalline TiO₂ (NC-TiO₂) film. Although many researchers reported the use of carbon based materials in DSSCs but most of them are carbon based counter electrodes [14,15] or carbon nanotube (CNT)-TiO₂ hybrid based working electrodes [16]. Two-dimensional flat graphene sheets incorporated with small TiO₂ nanoparticles (<10 nm) applied as an interfacial layer makes it unique compared to other carbon based materials such as CNT and carbon black to decrease the contact between FTO surface and electrolyte, thereby reducing the back-transport reaction of electrons in the FTO and NC-TiO₂ film interface.

2. Experimental

Graphene oxide (GO) was prepared through Hummer's method [17]. All chemicals and materials were used without any further purification. Graphene oxide was reduced by following procedure reported elsewhere [13]. Firstly, TiO₂ colloidal suspension (0.05 M) was prepared by drop wise addition of titanium (IV) isopropoxide (Fluka) to a vigorously stirred solution of ethanol. The colloidal suspension was continuously stirred prior to its use to prevent agglomeration of the particles. Graphene oxide (1.5 mg/ml) was added to the TiO₂ colloidal suspension and sonicated for

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30 min to disperse of GO sheets with TiO₂ particles. UV-assisted reduction of graphene oxide was performed by 450 W xenon arc lamp for about 2 h.

Reduced graphene–TiO₂ solution was spin coated over FTO glass (15 Ω/□, Solaronix SA) substrate at 1500 rpm for 30 s and the resulting film was annealed at 500 °C for about 30 min in argon atmosphere. Then TiO₂ paste (Degussa P25) was cast over graphene–TiO₂ interfacial layer by doctor blade technique and successive sintering at 500 °C for 30 min. The nanocrystalline TiO₂ film was sensitized with N719 solution (535-tris TBA, Solaronix, 13 mg dissolved in 50 ml ethanol) for 24 h. Pt coated FTO glass was used as counter electrode. The electrolyte used in DSSCs consists of 0.5 M LiI, 0.05 M I₂, 0.5 M 4-tert-butylpyridine in mixed solvent of acetonitrile and propylene carbonate (1:1). DSSCs without any interfacial layer were also prepared for comparison.

The transmittance of the interfacial films on FTO was measured by UV–Vis spectrophotometer (Hewlett Packard 8453). The DSSCs were illuminated under 100 mW/cm², AM 1.5 simulated sunlight by using 450 W xenon arc lamp (LH 151, Spectral Energy Co.). The incident light intensity was calibrated with a radiometer photometer (ILT 1400-A). Four samples for each with and without interfacial layer were made for *J*–*V* measurement, and the reproducibility of the effect of interfacial layer was quite good. The morphology of the graphene–TiO₂ interfacial layer was examined by an AFM (Xe-100, Park Systems) and a field emission scanning electron microscope (FE-SEM, JSM-6700, JEOL). Impedance spectra were measured by an impedance analyzer (IM6 ex, Zahner Elektrik). The spectra were scanned in a frequency range of 10⁻¹–10⁶ Hz at room temperature.

3. Results and discussion

Fig. 1a shows the change in color from light brown¹ to dark brown to black as the GO is reduced. The color change was caused by partial restoration of the π network within the carbon structure, as witnessed by the chemical reduction of GO sheets [18,19]. Charge separation occurs upon UV-irradiation of the TiO₂ particles [20]. In the presence of ethanol, the holes are scavenged to produce ethoxy radicals and electrons accumulate within TiO₂ particles. These accumulated electrons interact with GO sheets in order to reduce certain function groups [13]. The sheet resistance (*R*_s) of GO–TiO₂ layer on glass prior to UV-irradiation was 782.30 kΩ/□ using a four-point probe method. After 2 h of UV-irradiation, the sheet resistance became 17.30 kΩ/□. Since both samples (before and after UV-reduction) contained same concentration of TiO₂, the contribution of TiO₂ to the decrease of sheet resistance is expected to be constant.

The spin coated graphene–TiO₂ over the FTO glass substrate was analyzed by AFM. Fig. 1b shows the AFM image of a single graphene sheet of the graphene–TiO₂ composite. The graphene sheet is coupled with TiO₂ nanoparticles. The interaction of TiO₂ nanoparticles with graphene oxide sheets can be through physisorption, electrostatic binding or through charge transfer [21]. The line profile (Fig. 1c) of AFM image showed that the average height of TiO₂ particles on graphene sheet was <10 nm. However, some large particles ~20 nm in diameter were also observed. These large TiO₂ particles are attributed to agglomeration of TiO₂ colloids in the solution. The average rms surface roughness (*R*_a) of the commercial FTO (Fig. 2a) and graphene–TiO₂ interfacial layers were 15 and 6.26 nm, respectively. Graphene–TiO₂ interfacial layer coated the rough FTO layer, which led to more uniform surface, as shown in Fig. 2b. The cross-sectional SEM image in Fig. 2c showed that a

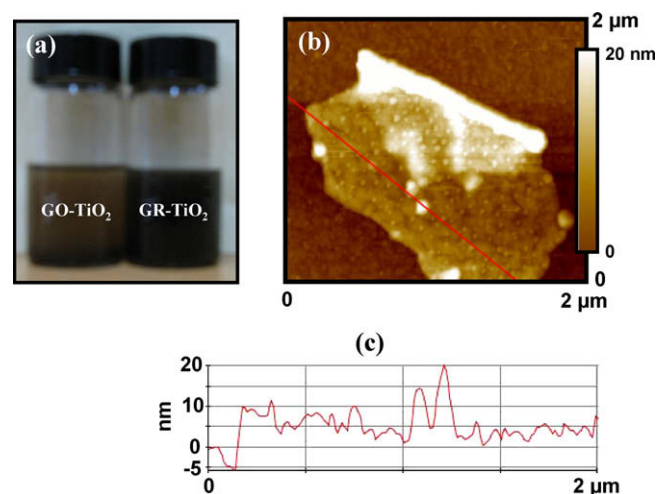


Fig. 1. (a) The changes of color of 0.05 M TiO₂ solution with 1.5 mg/ml GO before and after UV-irradiation for 2 h, (b) AFM images of GO–TiO₂ nanocomposites films (size of 2 μm × 2 μm) over FTO substrate and (c) line profile of the AFM image of GO–TiO₂ composite.

graphene–TiO₂ interfacial layer with a thickness of 500 nm was adhered tightly to the FTO layer. In comparison, significant amount of voids were observed between the FTO surface and NC–TiO₂ film for the DSSCs without any interfacial layer (not shown here).

Fig. 3a shows the transmittance spectra of the bare FTO and graphene–TiO₂ interfacial layers coated on the FTO substrate. The transmittance of the bare FTO substrate was ~82%, which decreased to 75% by the introduction of graphene–TiO₂ interfacial layer over FTO. However, the transmittance of the graphene–TiO₂/FTO substrate was high enough to use in DSSC.

The influence of the graphene–TiO₂ interfacial layer on the performance of the DSSCs was investigated. Fig. 3b shows the *J*–*V* characteristic curves. The cells with graphene–TiO₂ interfacial layer showed a considerably improved open-circuit voltage (*V*_{oc}), compared to that of the cell without interfacial layer. With the use of graphene interfacial layer, the open-circuit voltage increased from 0.687 (±0.003) V to 0.741 (±0.005) V but the fill factor remained almost same. A small decrease in the short-circuit current density (*J*_{sc}) was observed and this may be due to the decrease in visible light transmittance of the electrode from 82% to 75% (Fig. 3a) with the introduction of graphene–TiO₂ interfacial layer. The photoconversion efficiency increased from 4.89% to 5.26% with graphene–TiO₂ interfacial layer. Also, the DSSC with graphene–TiO₂ interfacial layer showed a substantial reduction of dark (back-transport reaction) current in *J*–*V* curves under dark conditions (not shown here). The Nyquist plots (Fig. 3c) measured in the dark under a forward bias of –0.7 V, showed the radius of the middle semicircle increased with the introduction of graphene–TiO₂ interfacial layer, indicating that the electron recombination resistance augments with the interfacial layer.

As mentioned earlier, a thick TiO₂ layer formed by the doctor blade method cannot cover the rough FTO surface uniformly without void formation because of the rough surface of FTO layer. Iodide (I⁻) ions in the electrolyte migrate from the counter electrode to the nanopores of TiO₂ transfer the electrons to the highest occupied molecular orbital level of the dye adsorbed on TiO₂ and then converted to I₃⁻ ions. Some of the I₃⁻ ions in the electrolyte penetrate the porous TiO₂ and can directly contact with FTO surface, thereby collecting the electrons from the FTO surface through back-transport reaction [22]. As shown in Fig. 4, the presence of the graphene–TiO₂ interfacial layer between FTO and NC–TiO₂ in the DSSC may inhibit the direct contact between I₃⁻ ions and FTO electrode, thereby effectively preventing the back-trans-

¹ For interpretation of color in Fig. 1, the reader is referred to the web version of this article.

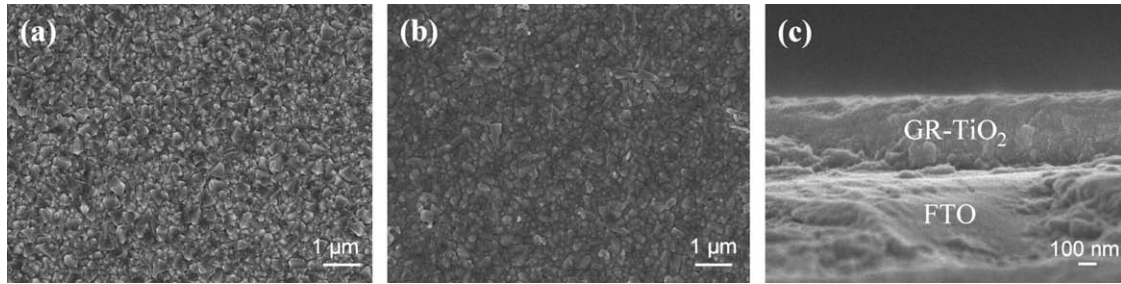


Fig. 2. FE-SEM surface images of (a) bare FTO surface and (b) TiO₂-GO interfacial layer over FTO. (c) Cross-sectional images of the TiO₂-GO interfacial layer.

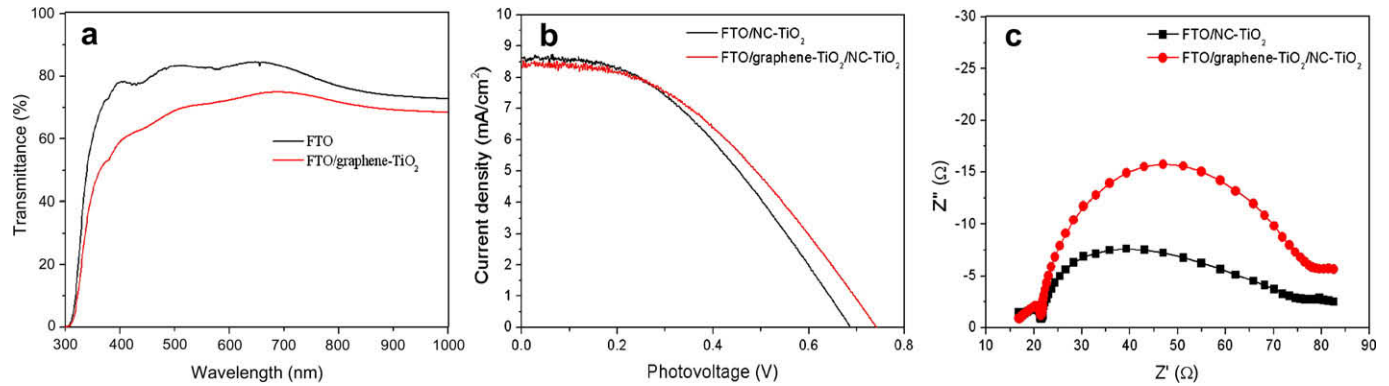


Fig. 3. (a) UV-Vis transmission spectrum of bare FTO and graphene-TiO₂ coated FTO substrate, (b) *J*-*V* characteristics curves and (c) impedance spectra (Nyquist plots) of the DSSCs with and without graphene-TiO₂ interfacial layer.

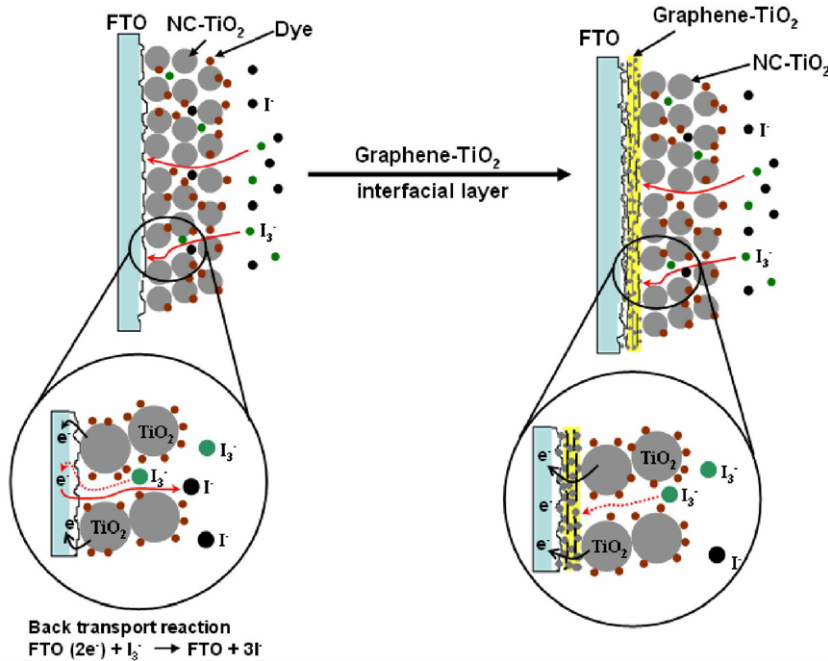


Fig. 4. Schematic representation and mechanism of applied graphene-TiO₂ interfacial layer to prevent back-transport reaction of electrons.

port of electrons from the FTO electrode to the I₃⁻ ions and thus increasing *V*_{oc}.

By introducing graphene-TiO₂ interfacial layer in the DSSCs, the open-circuit voltage (*V*_{oc}) increased. Therefore it can be stated that, the back-transport of electrons from the FTO electrode to the I₃⁻ ions was suppressed by the introduction of graphene-TiO₂ interfacial layer. Two-dimensional graphene sheet acts a barrier between

FTO layer and electrolyte and thus increasing the open-circuit photovoltage (*V*_{oc}).

4. Conclusion

Graphene oxide in the GO-TiO₂ nanocomposites was successfully reduced by UV-assisted photocatalytic reduction. The reduced

graphene–TiO₂ nanocomposites were applied as interfacial layer between FTO and nanocrystalline TiO₂ layer in DSSCs. The low roughness of graphene–TiO₂ interfacial layer provided better adhesion between the FTO substrate and NC-TiO₂ layer than without any interfacial layer. The introduction of 500 nm thick graphene–TiO₂ interfacial layer resulted in a 54 mV increase in the open-circuit voltage (V_{oc}) due to retardation of the back-transport reaction in the FTO/TiO₂ interface. It is believed that the two-dimensional graphene sheets significantly decrease the direct contact of the electrolyte with the FTO substrate. The photoconversion efficiency increased from 4.89% to 5.26% after introducing the graphene–TiO₂ interfacial layer.

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Appendix A. Supplementary material

Supplementary data associated with this article can be found, in the online version, at doi:10.1016/j.cplett.2009.10.066.

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